

N-Channel 8-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
8	0.011 at $V_{GS} = 4.5$ V	12	19 nC
	0.013 at $V_{GS} = 2.5$ V	12	
	0.016 at $V_{GS} = 1.8$ V	12	
	0.022 at $V_{GS} = 1.5$ V	12	
	0.041 at $V_{GS} = 1.2$ V	12	

FEATURES

- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912

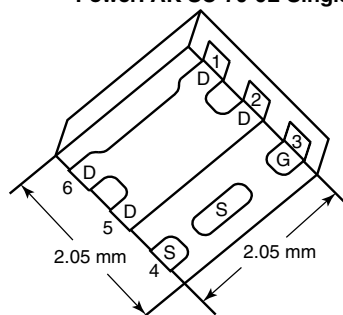


RoHS
COMPLIANT
HALOGEN
FREE

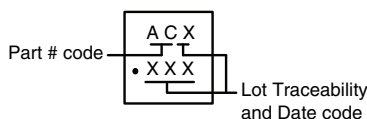
APPLICATIONS

- Load Switch for Portable Applications

PowerPAK SC-70-6L-Single

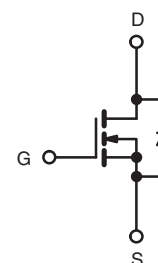


Marking Code



Ordering Information:

[SiA414DJ-T4-GE3](#) (Lead (Pb)-free and Halogen-free)
[SiA414DJ-T1-GE3](#) (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	8	V
Gate-Source Voltage		V_{GS}	± 5	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	I_D	12 ^a	A
	$T_C = 70$ °C		12 ^a	
	$T_A = 25$ °C		12 ^{a, b, c}	
	$T_A = 70$ °C		11.6 ^{b, c}	
Pulsed Drain Current		I_{DM}	40	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	I_S	12 ^a	
	$T_A = 25$ °C		2.9 ^{b, c}	
Maximum Power Dissipation	$T_C = 25$ °C	P_D	19	W
	$T_C = 70$ °C		12	
	$T_A = 25$ °C		3.5 ^{b, c}	
	$T_A = 70$ °C		2.2 ^{b, c}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}			260	

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	$t \leq 5$ s	R_{thJA}	28	36	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	5.3	6.5	

Notes:

- Package limited
- Surface mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- See solder profile (www.vishay.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 80 °C/W.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	8			V	
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		9		mV/°C	
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 3			
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.35		0.8	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 5 V			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 8 V, V _{GS} = 0 V			1	μA	
		V _{DS} = 8 V, V _{GS} = 0 V, T _J = 55 °C			10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 4.5 V	20			A	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 9.7 A		0.009	0.011	Ω	
		V _{GS} = 2.5 V, I _D = 9 A		0.011	0.013		
		V _{GS} = 1.8 V, I _D = 8.1 A		0.013	0.016		
		V _{GS} = 1.5 V, I _D = 4.5 A		0.016	0.022		
		V _{GS} = 1.2 V, I _D = 2.4 A		0.027	0.041		
Forward Transconductance ^a	g _{fs}	V _{DS} = 4 V, I _D = 9.7 A		50		S	
Dynamic ^b							
Input Capacitance	C _{iss}	V _{DS} = 4 V, V _{GS} = 0 V, f = 1 MHz		1800		pF	
Output Capacitance	C _{oss}			650			
Reverse Transfer Capacitance	C _{rss}			450			
Total Gate Charge	Q _g	V _{DS} = 4 V, V _{GS} = 5 V, I _D = 10 A		21	32	nC	
		V _{DS} = 4 V, V _{GS} = 4.5 V, I _D = 10 A		19	29		
					2.5		
					6.5		
Gate-Source Charge	Q _{gs}						
Gate-Drain Charge	Q _{gd}						
Gate Resistance	R _g	f = 1 MHz		2.5		Ω	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 4 V, R _L = 0.4 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω		12	20	ns	
Rise Time	t _r			10	15		
Turn-Off Delay Time	t _{d(off)}			65	100		
Fall Time	t _f			20	30		
Turn-on Delay Time	t _{d(on)}	V _{DD} = 4 V, R _L = 0.4 Ω I _D ≅ 10 A, V _{GEN} = 5 V, R _g = 1 Ω		10	15		
Rise Time	t _r			10	15		
Turn-Off Delay Time	t _{d(off)}			35	55		
Fall Time	t _f			10	15		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			12	A	
Pulse Diode Forward Current	I _{SM}				40		
Body Diode Voltage	V _{SD}	I _S = 10 A, V _{GS} = 0 V		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C		40	80	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			20	40	nC	
Reverse Recovery Fall Time	t _a			12		ns	
Reverse Recovery Rise Time	t _b			28			

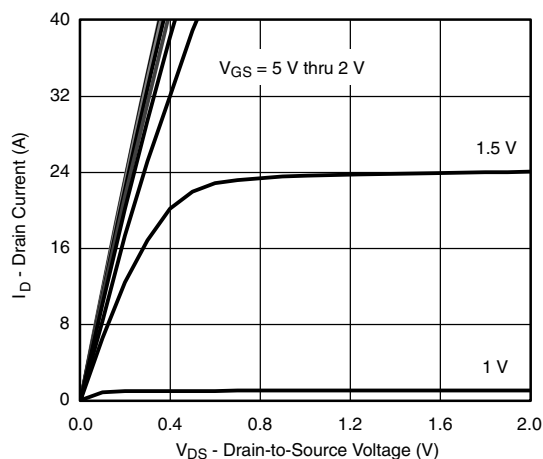
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

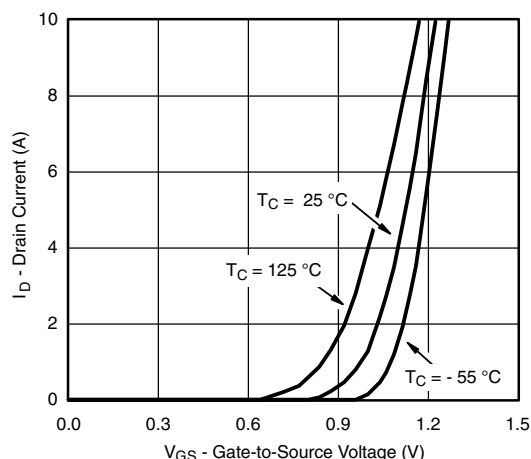
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

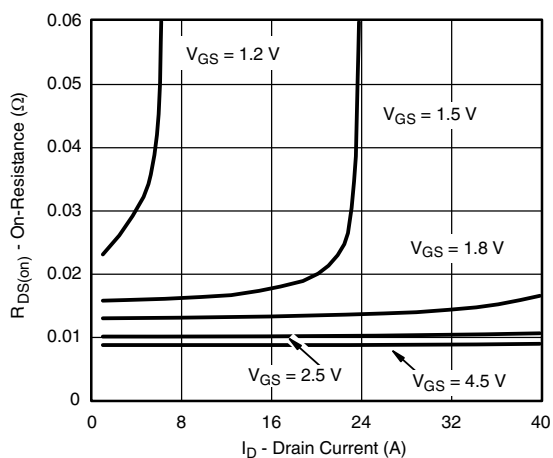
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



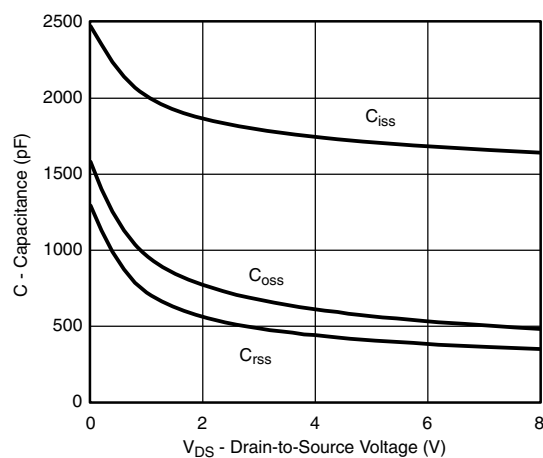
Output Characteristics



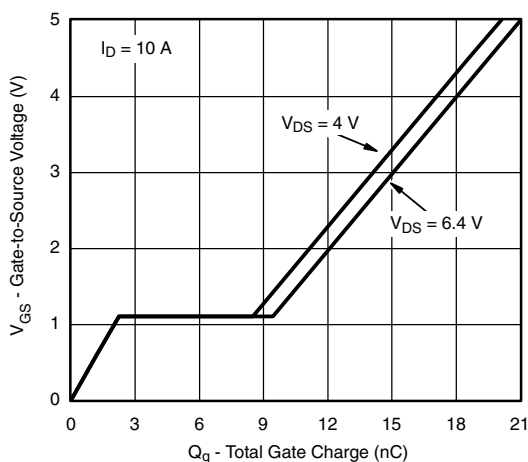
Transfer Characteristics



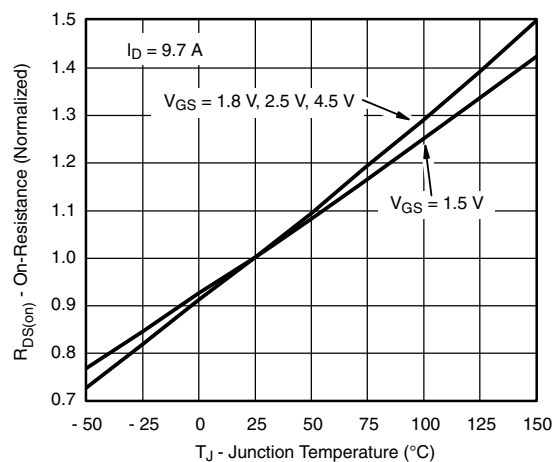
On-Resistance vs. Drain Current and Gate Voltage



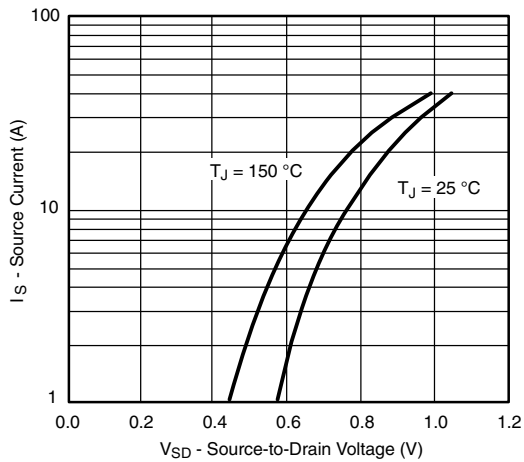
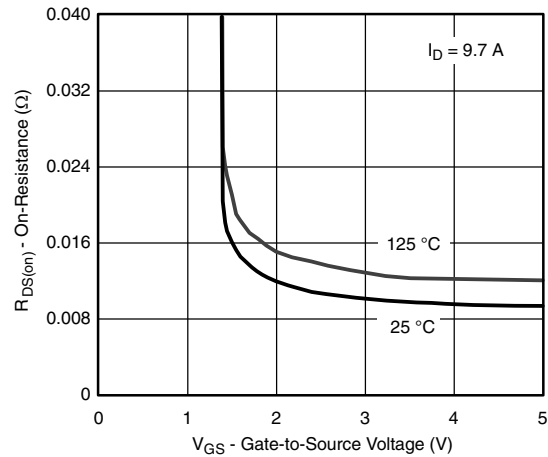
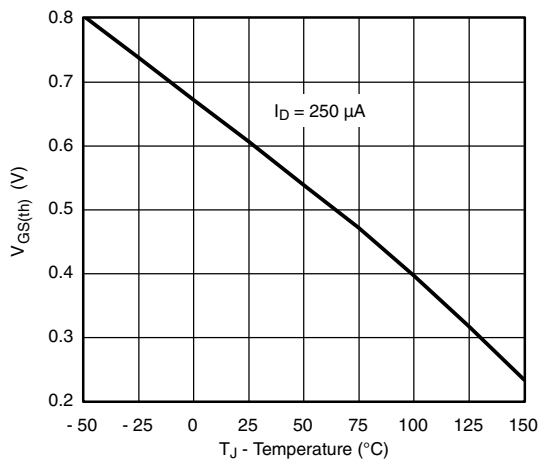
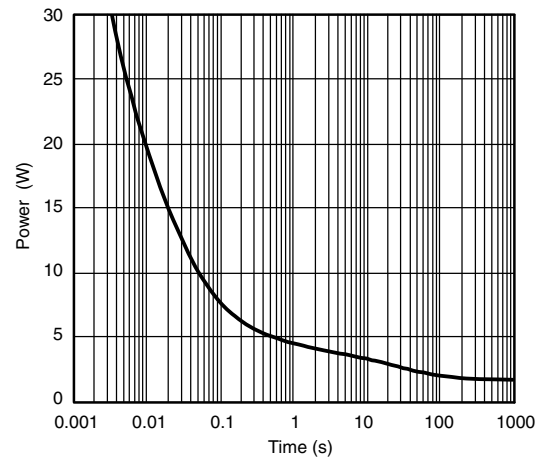
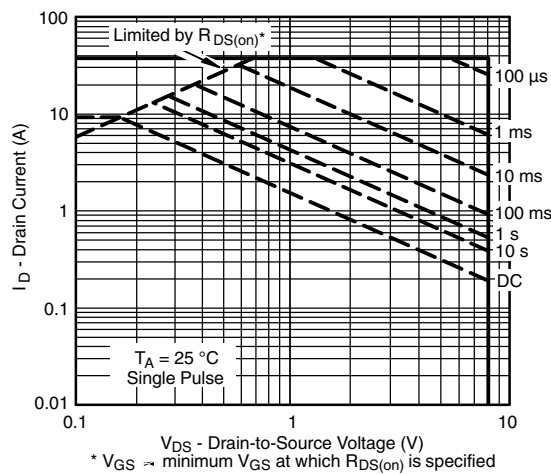
Capacitance



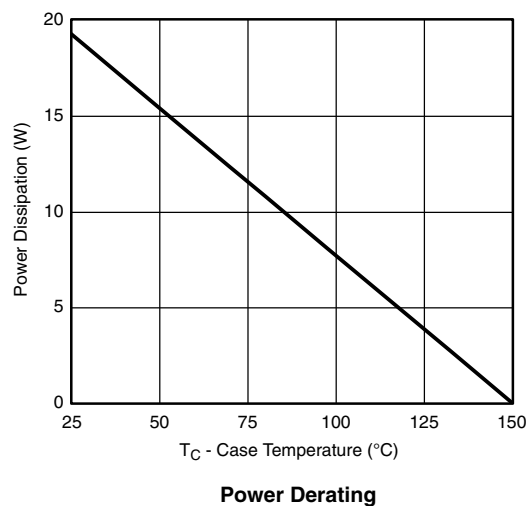
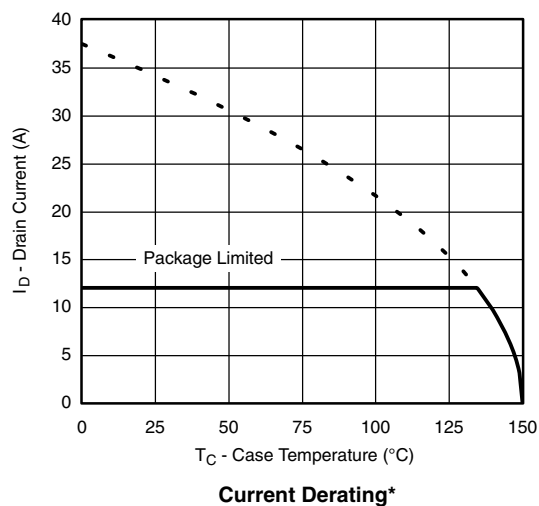
Gate Charge



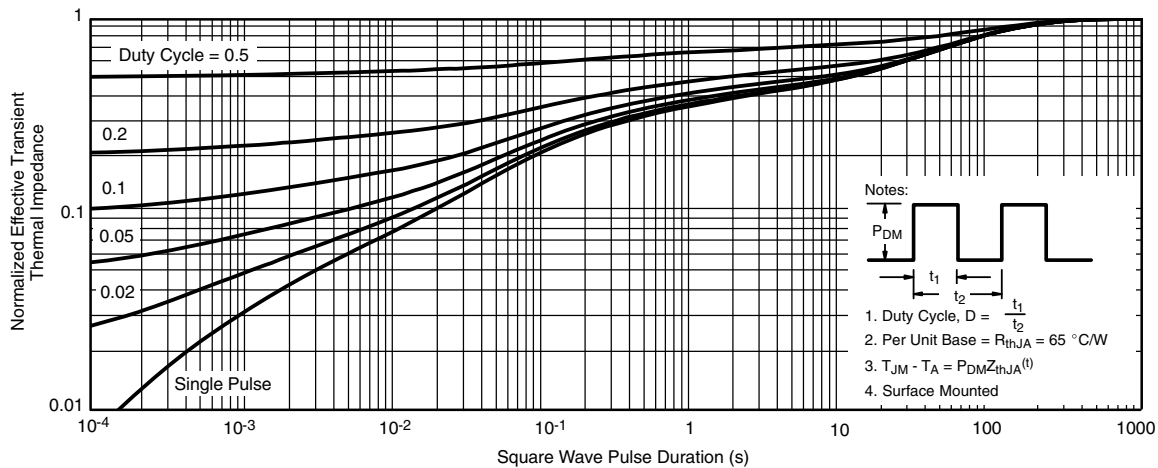
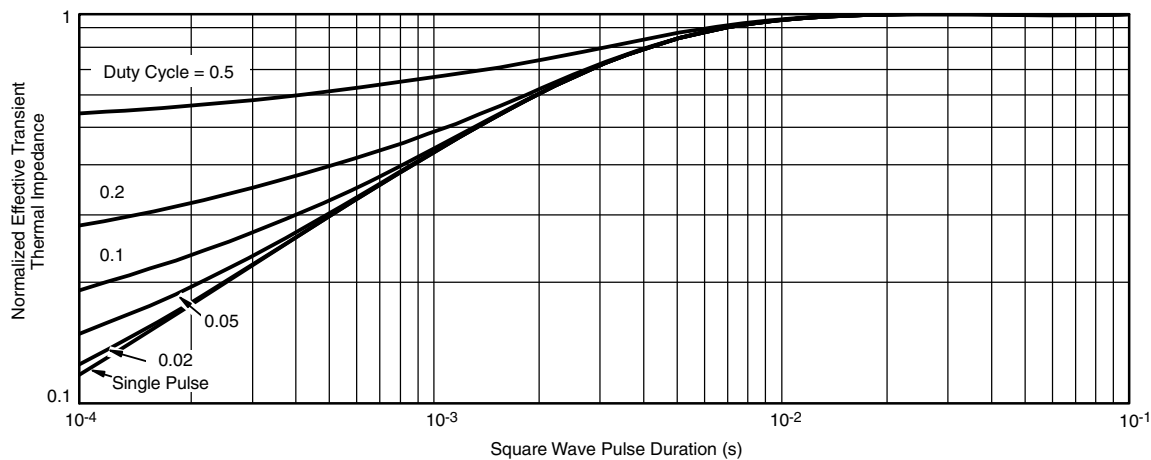
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power (Junction-to-Ambient)****Safe Operating Area, Junction-to-Ambient**

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



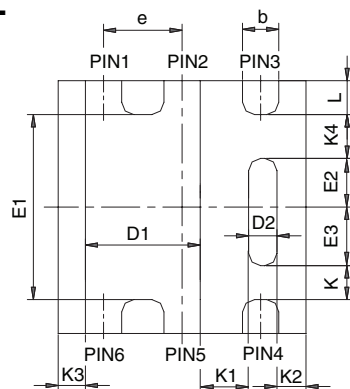
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Case**

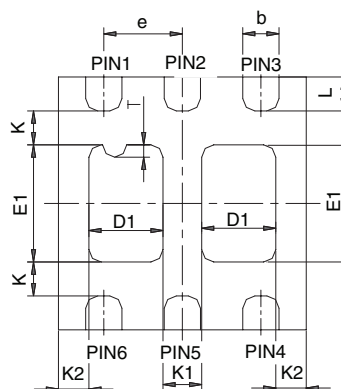
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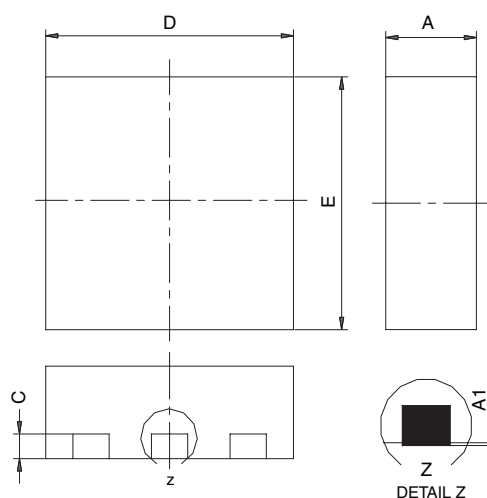
PowerPAK® SC70-6L



BACKSIDE VIEW OF SINGLE



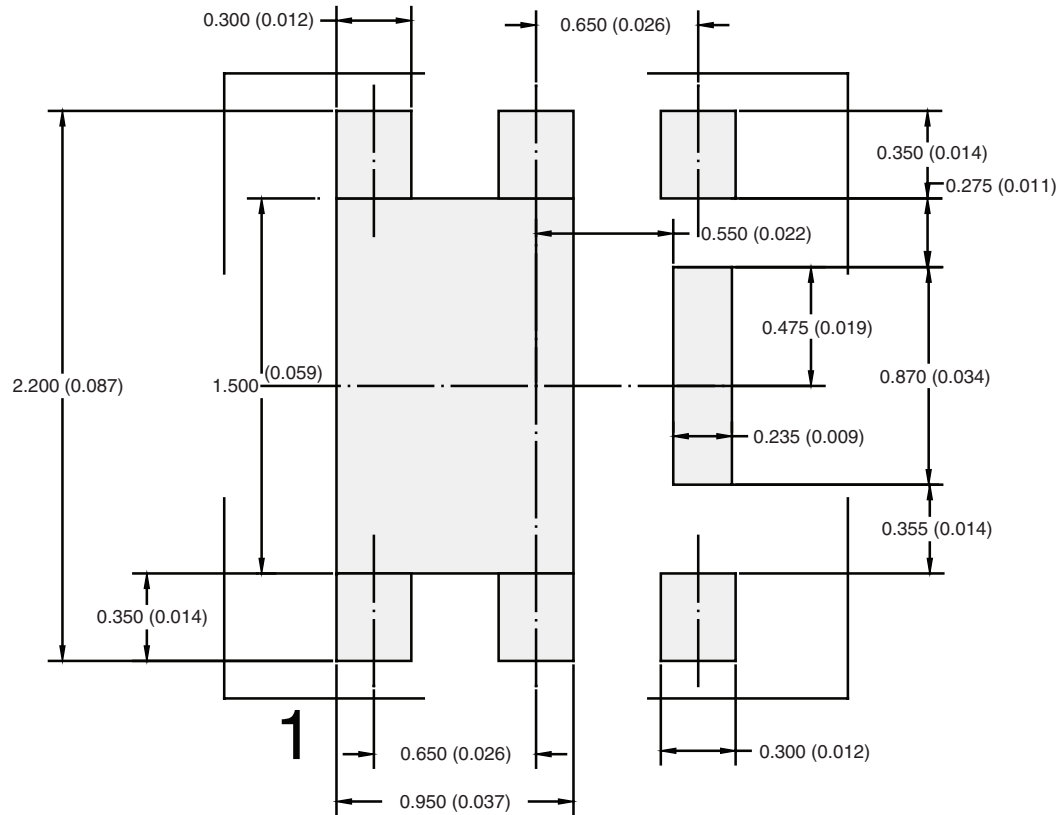
BACKSIDE VIEW OF DUAL



- Notes:
1. All dimensions are in millimeters
 2. Package outline exclusive of mold flash and metal burr
 3. Package outline inclusive of plating

DIM	SINGLE PAD						DUAL PAD					
	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
A	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
C	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
e	0.65 BSC			0.026 BSC			0.65 BSC			0.026 BSC		
K	0.275 TYP			0.011 TYP			0.275 TYP			0.011 TYP		
K1	0.400 TYP			0.016 TYP			0.320 TYP			0.013 TYP		
K2	0.240 TYP			0.009 TYP			0.252 TYP			0.010 TYP		
K3	0.225 TYP			0.009 TYP								
K4	0.355 TYP			0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006
ECN: C-07431 – Rev. C, 06-Aug-07 DWG: 5934												

RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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<http://moschip.ru/get-element>

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9